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<u>Vishay Semiconductor/Diodes Division</u> <u>VS-HFA16PB120PBF</u>

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VS-HFA16PB120PbF, VS-HFA16PB120-N3

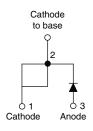
Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 16 A



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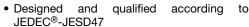
TO-247AC modified



PRODUCT SUMMARY						
Package	TO-247AC modified (2 pins)					
I _{F(AV)}	16 A					
V _R	1200 V					
V _F at I _F	2.3 V					
t _{rr} typ.	30 ns					
T _J max.	150 °C					
Diode variation	Single die					

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}









ROHS
COMPLIANT
HALOGEN
FREE
Available

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA16PB120... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A continuous current, the VS-HFA16PB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16PB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V_R		1200	V		
Maximum continuous forward current	I _F	T _C = 100 °C	16			
Single pulse forward current	I _{FSM}		190	Α		
Maximum repetitive forward current	I _{FRM}		64			
Maximum nauga dissination	P _D	T _C = 25 °C	151	W		
Maximum power dissipation		T _C = 100 °C	60] vv		
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C		

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	Ι _R = 100 μΑ		1200	-	-	
Maximum forward voltage		I _F = 16 A	See fig. 1	-	2.5	3.0	V
	V _{FM}	I _F = 32 A		-	3.2	3.93	
		I _F = 16 A, T _J = 125 °C		-	2.3	2.7	
Maximum reverse		V _R = V _R rated	Coo fig. 0	-	0.75	20	μА
leakage current	I _{RM}	T _J = 125 °C, V _R = 0.8 x V _R rated	See fig. 2	-	375	2000	
Junction capacitance	C _T	V _R = 200 V	See fig. 3	-	27	40	pF
Series inductance	L _S	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	A/μs, V _R = 30 V	-	30	-	
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C	I _F = 16 A dI _F /dt = 200 A/μs V _R = 200 V	-	90	135	ns
555 fig. 5, 15	t _{rr2}	T _J = 125 °C		-	164	245	
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	5.8	10	- A - nC
See fig. 6	I _{RRM2}	T _J = 125 °C		-	8.3	15	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	260	675	
See fig. 7	Q _{rr2}	T _J = 125 °C		-	680	1838	
Peak rate of fall of recovery current during t _b See fig. 8	dI _{(rec)M} /dt1	T _J = 25 °C		-	120	ı	- A/µs
	dI _{(rec)M} /dt2	T _J = 125 °C		-	76	-	AνμS

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R _{thJC}		-	-	0.83	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.50	-	
Weight			-	2.0	-	g
vveigni			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-247AC modified (JEDEC)	HFA16PB120			





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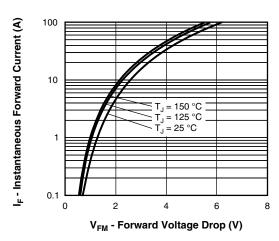


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

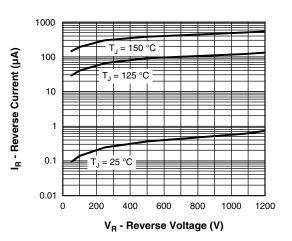


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

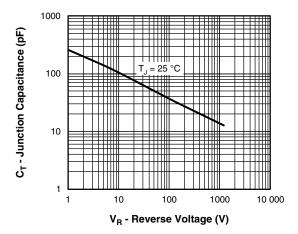


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

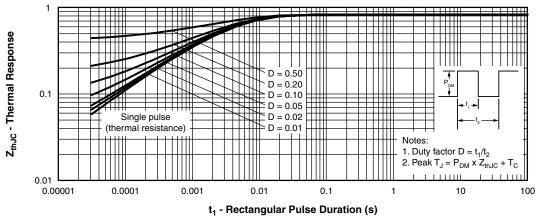


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

1600



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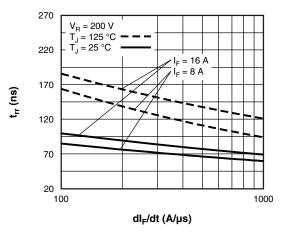
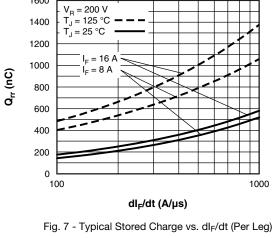


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt (Per Leg)



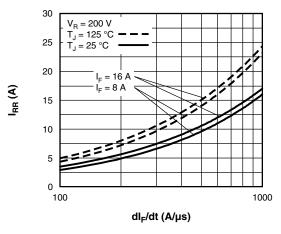


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

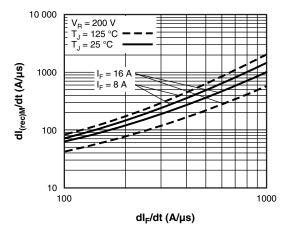


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt (Per Leg)

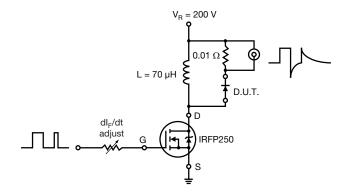


Fig. 9 - Reverse Recovery Parameter Test Circuit

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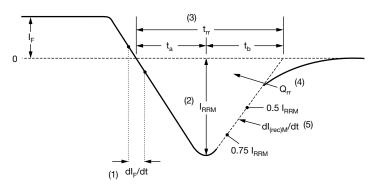
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- (1) dl_E/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

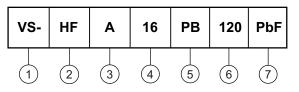
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- HEXFRED® family
- Electron irradiated
- Current rating (16 = 16 A)
- PB = TO-247AC modified
- Voltage rating: (120 = 1200 V)
- Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-HFA16PB120PbF	25	500	Antistatic plastic tube				
VS-HFA16PB120-N3	25	500	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS						
Dimensions		www.vishay.com/doc?95541				
Part marking information	TO-247AC modified PbF	www.vishay.com/doc?95255				
Fait marking imormation	TO-247AC modified -N3	www.vishay.com/doc?95442				
SPICE model		www.vishay.com/doc?95672				

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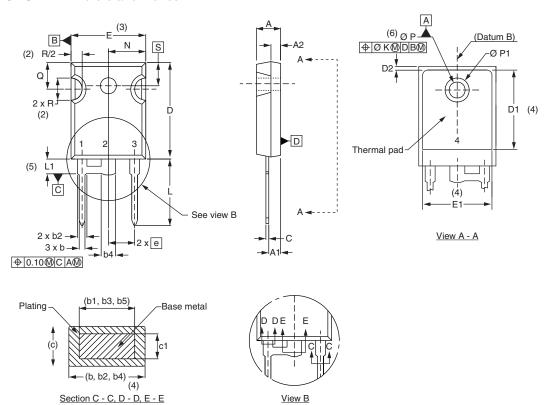


Outline Dimensions

Vishay Semiconductors

TO-247 modified

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	MILLIMETERS		INCHES	
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
Е	15.29	15.87	0.602	0.625	3
E1	13.72	-	0.540	•	
е	5.46	BSC	0.215	BSC	
ØK	2.	2.54		0.010	
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
N	7.62	7.62 BSC		.3	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51	BSC	0.217 BSC		

Notes

- (1) Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c

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